

STPS60SM200C

Power Schottky rectifier

Features

- High reverse voltage (200 V)
- Low forward voltage drop
- High frequency operation

Description

The STPS60SM200C is a dual Schottky rectifier suited for high frequency switched-mode power supply.

Housed in TO-247, this device is especially suited for use in telecom base station SMPS, providing these applications with a good efficiency at both low and high load.

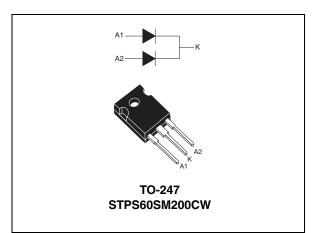


Table 1. Device summary

Symbol	Value
I _{F(AV)}	2 x 30 A
V _{RRM}	200 V
T _j (max)	175 °C
V _F (typ)	640 mV

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1 Characteristics

Table 2. Absolute ratings (limiting values per diode at 25 °C, unless otherwise specified)

Pa	Value	Unit			
Repetitive peak reverse voltage			200	V	
Forward current rms			50	А	
Average forward autrent S = 0.5	Per diode, $\delta = 0.5$	T _c = 155 °C	30	۸	
$I_{F(AV)}$ Average forward current $\delta = 0.5$	per device, $\delta = 0.5$	T _c = 150 °C	60	A	
Surge non repetitive forward current $t_p = 10$ ms sinusoidal, $T_c = 25$ °C			500	А	
Storage temperature range -65 to + 175				°C	
Maximum operating junction temperature ⁽¹⁾ -40 to + 17			-40 to + 175	°C	
	Repetitive peak reverse voltage Forward current rms Average forward current $\delta = 0.5$ Surge non repetitive forward current Storage temperature range	$\begin{tabular}{lllllllllllllllllllllllllllllllllll$	$\label{eq:rescaled} \hline Per diode, \ \delta = 0.5 \qquad \hline T_c = 155 \ ^\circ C \\ \hline per device, \ \delta = 0.5 \qquad \hline T_c = 150 \ ^\circ C \\ \hline Surge non repetitive forward current \ t_p = 10 \ ms \ sinusoidal, \ T_c = 25 \ ^\circ C \\ \hline Storage temperature range \\ \hline \hline \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$	Repetitive peak reverse voltage200Forward current rms50Average forward current $\delta = 0.5$ Per diode, $\delta = 0.5$ $T_c = 155 \text{ °C}$ 30Average forward current $\delta = 0.5$ $per device, \delta = 0.5$ $T_c = 150 \text{ °C}$ 60Surge non repetitive forward current $t_p = 10 \text{ ms sinusoidal}, T_c = 25 \text{ °C}$ 500Storage temperature range-65 to + 175	

 $1. \quad \frac{dPtot}{dTj} < \frac{1}{Rth(j-a)} \text{ condition to avoid thermal runaway for a diode on its own heatsink}$

Table 3. Thermal resistance

Symbol	Parameter		Value	Unit
P	Junction to case	Per diode	0.7	
R _{th(j-c)}	Sunction to case	Total	0.5	°C/W
R _{th(c)}	Coupling		0.3	

When the two diodes 1 and 2 are used simultaneously:

 ΔT_{j} (diode 1) = P(diode 1) x R_{th(j-c)}(Per diode) + P(diode 2) x R_{th(c)}

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _B ⁽¹⁾	Povorco lookago ourront	T _j = 25 °C	V - V			0.05	mA
'R` ´	I _R ⁽¹⁾ Reverse leakage current	T _j = 125 °C	$V_{R} = V_{RRM}$		6	13	ША
	$V_{F}^{(2)} Forward voltage drop Forward voltage drop = \frac{T_{j} = 25 \ ^{\circ}C}{T_{j} = 125 \ ^{\circ}C} I_{F} = 7.5 \ A$ $\frac{T_{j} = 25 \ ^{\circ}C}{T_{j} = 125 \ ^{\circ}C} I_{F} = 15 \ A$ $\frac{T_{j} = 25 \ ^{\circ}C}{T_{j} = 25 \ ^{\circ}C} I_{F} = 30 \ A$		0.67	0.70			
		T _j = 125 °C	ι _F – 7.3 Α		0.51	0.55	
V (2)		T _j = 25 °C	I _F = 15 A		0.73	0.77	V
۷F		T _j = 125 °C			0.57	0.61	v
		T _j = 25 °C	I_ = 30 A		0.79	0.83	
		$T_j = 125 \text{ °C}$	$I_F = 30 A$		0.64	0.69	

1. Pulse test: $t_p = 5 \text{ ms}, \delta < 2\%$

2. Pulse test: $t_p = 380 \ \mu s, \ \delta < 2\%$

To evaluate the conduction losses use the following equation:

 $P = 0.58 \text{ x } I_{F(AV)} + 0.0037 \text{ x } I_{F}^{2}(RMS)$



Figure 1. Average forward power dissipation Figure 2. versus average forward current (per diode)

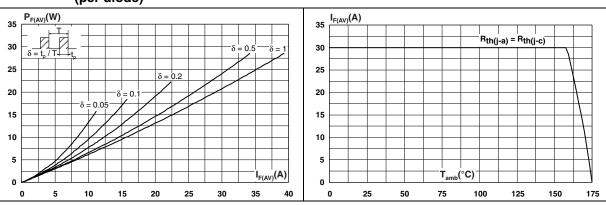


Figure 3. Non repetitive surge peak forward current versus overload duration (maximum values, per diode)

Figure 4. Relative variation of thermal impedance junction to case versus pulse duration

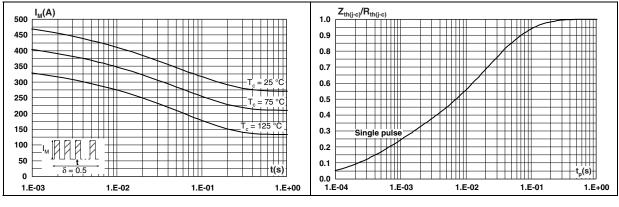
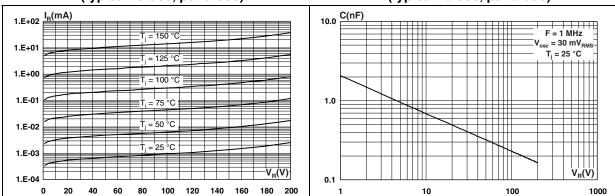


Figure 5. Reverse leakage current versus reverse voltage applied (typical values, per diode)

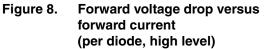
Figure 6. Junction capacitance versus reverse voltage applied (typical values, per diode)

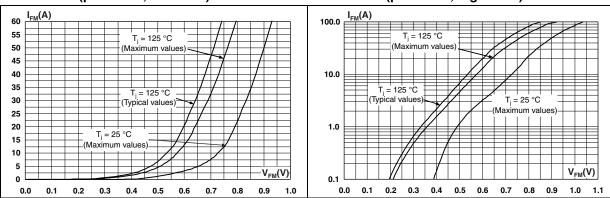


. Average forward current versus ambient temperature (δ = 0.5)



Figure 7. Forward voltage drop versus forward current (per diode, low level)







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2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 to 1.0 N·m

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Table 5. TO-247 dimensions

		Dimensions			
	Ref.	Millimeters		Inches	
		Min.	Max.	Min.	Max.
	Α	4.85	5.16	0.191	0.203
	D	2.20	2.60	0.086	0.102
	Е	0.40	0.80	0.015	0.031
	F	1.00	1.40	0.039	0.055
	F1	3.00) typ.	0.118	8 typ.
H A	F2	2.00) typ.	0.079	9 typ.
	F3	1.90	2.40	0.075	0.094
	F4	3.00	3.40	0.118	0.134
	G	10.90 typ.		0.429 typ.	
	Н	15.45	16.03	0.608	0.631
	L	19.85	21.09	0.781	0.830
$F_{1} \xrightarrow{F_{1}} F_{2} \xrightarrow{F_{2}} F_{2} \xrightarrow{F_{1}} F_{2} \xrightarrow{F_{2}} F_{3} \xrightarrow{F_{2}} F_{4} \xrightarrow{F_{4}} F_{4$	L1	3.70	4.30	0.146	0.169
V_2 F_4 D	L2	18.30	19.13	0.720	0.753
F(x3) M	L3	14.20	20.30	0.559	0.799
G G	L4	34.05	41.38	1.341	1.629
	L5	5.35	6.30	0.211	0.248
	М	2.00	3.00	0.079	0.118
	V	5°	typ.	5° 1	typ.
	V2	60°	typ.	60°	typ.
	Dia.	3.55	3.65	0.140	0.144

3 Ordering information

Table 6.Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS60SM200CW	STPS60SM200CW	TO-247	4.45 g	30	Tube

4 Revision history

Table 7.Document revision history

Date	Revision	Changes
17-May-2011	1	First issue.



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